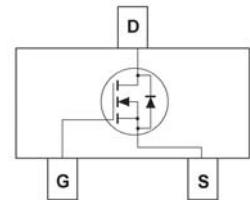


N-Channel Enhancement Mode MOSFET

Feature

- 30V/3.2A, $R_{DS(ON)} = 35\text{m}\Omega(\text{MAX})$ @ $V_{GS} = 10\text{V}$.
 $R_{DS(ON)} = 40\text{m}\Omega(\text{MAX})$ @ $V_{GS} = 4.5\text{V}$.
 $R_{DS(ON)} = 55\text{m}\Omega(\text{MAX})$ @ $V_{GS} = 2.5\text{V}$.
- Super High dense cell design for extremely low $R_{DS(ON)}$.
- Reliable and Rugged.
- SOT-23 for Surface Mount Package.



SOT-23

Applications

- Power Management
- Portable Equipment and Battery Powered Systems.

Absolute Maximum Ratings

$T_A=25^\circ\text{C}$ Unless Otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous	I_D	3.2	A

Electrical Characteristics

$T_A=25^\circ\text{C}$ Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
Off Characteristics						
Drain to Source Breakdown Voltage	BVDSS	$V_{GS}=0\text{V}$, $I_D=250\mu\text{A}$	30	-	-	V
Zero-Gate Voltage Drain Current	IDSS	$V_{DS}=30\text{V}$, $V_{GS}=0\text{V}$	-	-	1	μA
Gate Body Leakage Current, Forward	IGSSF	$V_{GS}=12\text{V}$, $V_{DS}=0\text{V}$	-	-	100	nA
Gate Body Leakage Current, Reverse	IGSSR	$V_{GS}=-12\text{V}$, $V_{DS}=0\text{V}$	-	-	-100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{GS}=V_{DS}$, $I_D=250\mu\text{A}$	0.6	-	1.5	V
Static Drain-source On-Resistance	RDS(ON)	$V_{GS}=10\text{V}$, $I_D=5.8\text{A}$	-	30	35	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}$, $I_D=5\text{A}$	-	33	40	$\text{m}\Omega$
		$V_{GS}=2.5\text{V}$, $I_D=4\text{A}$	-	45	55	$\text{m}\Omega$
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Voltage	VSD	$V_{GS}=0\text{V}$, $I_S=1.25\text{A}$	-	-	1.2	V

Typical Characteristics

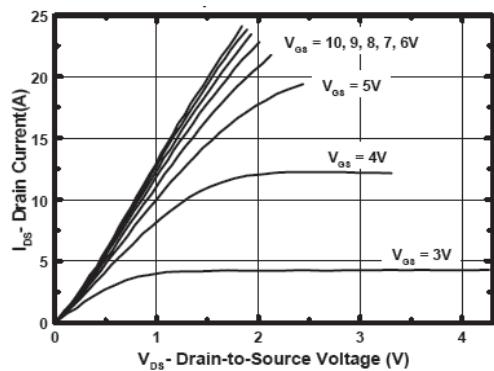


Figure 1. Output Characteristics

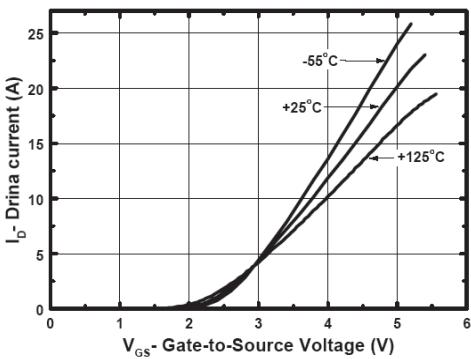


Figure 2. Transfer Characteristics

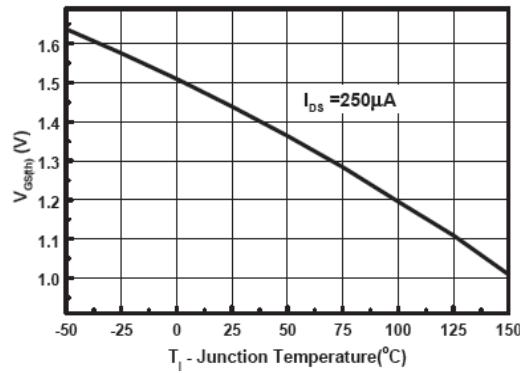


Figure 3. Gate Threshold Variation with Temperature

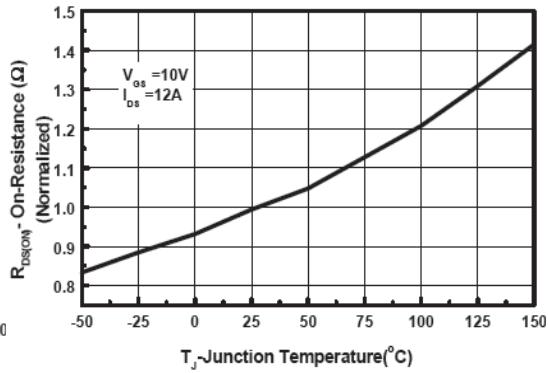


Figure 4. On-Resistance Variation with Temperature

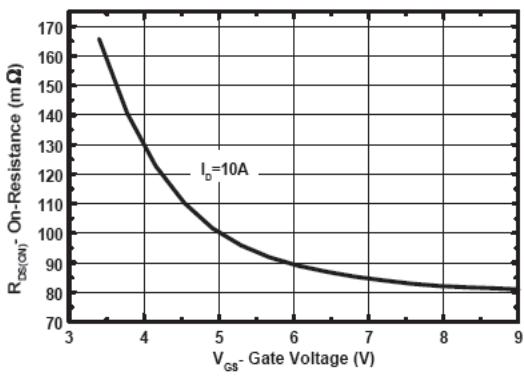


Figure 5. On-Resistance vs. Gate-to-Source Voltage

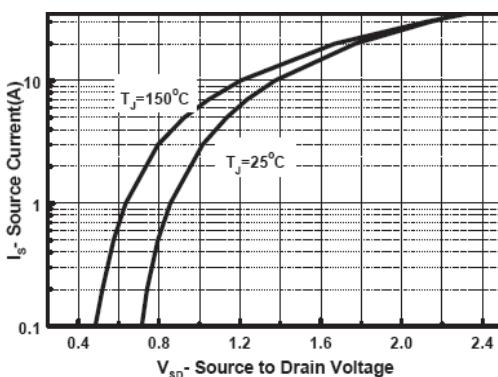
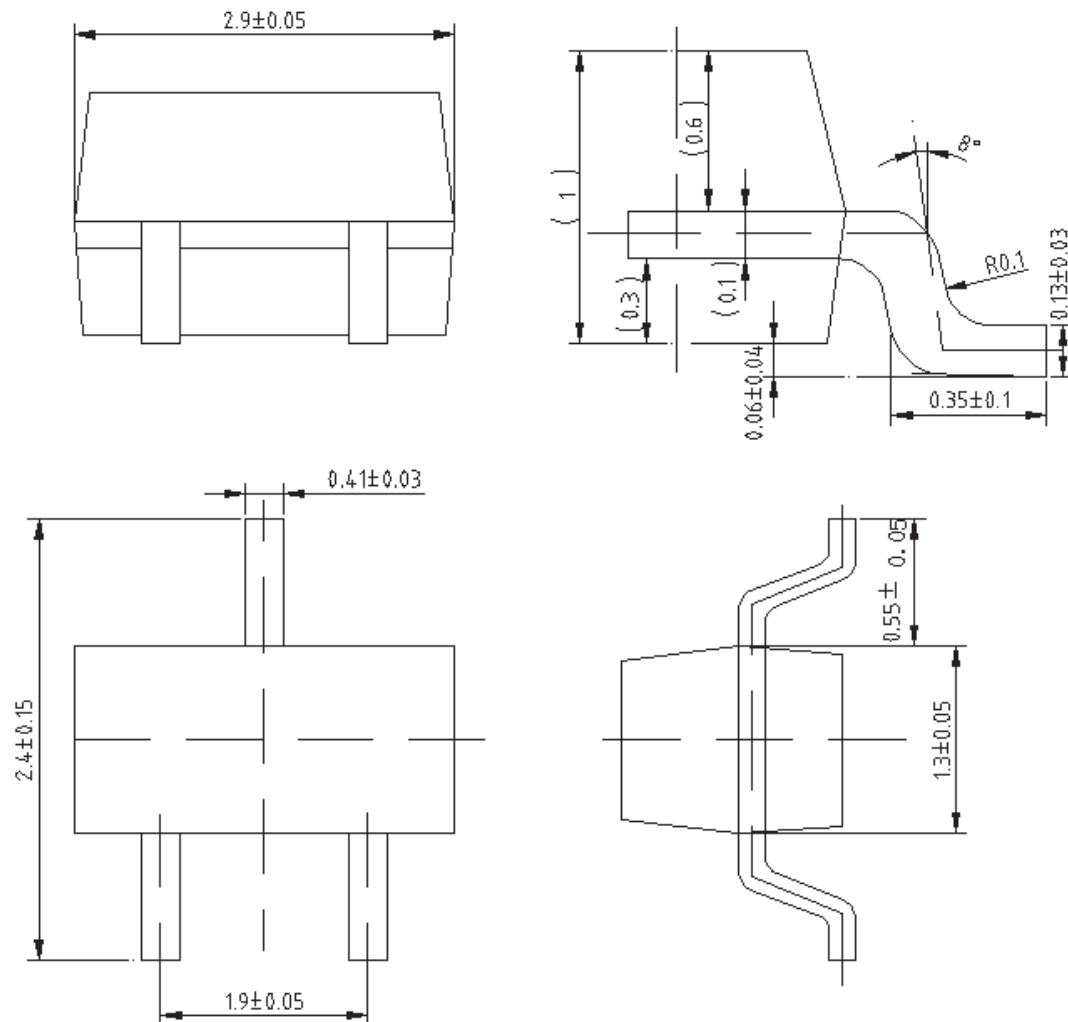


Figure 6. Source-Drain Diode Forward Voltage

Package Outline Dimensions (UNIT: mm)

SOT-23



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